



Dual N-Ch Fast Switching MOSFETs

- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary



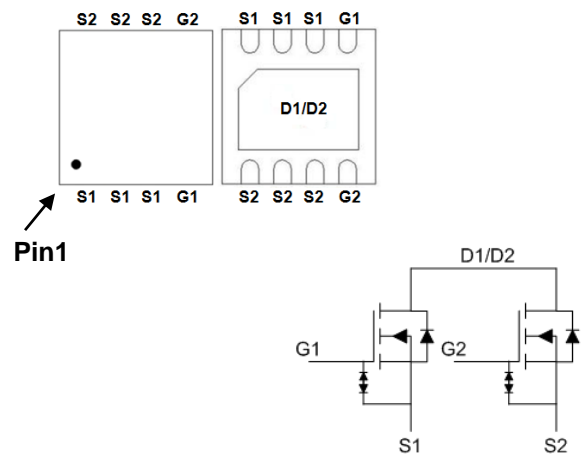
BVDSS	RDSON	ID
20V	8mΩ	8A

General Description

The PW2008 is the highest performance trench N-ch MOSFETs with extreme high cell density, which provide excellent RDSON and gate charge for most of the small power switching and load switch applications.

The PW2008 meet the RoHS and Green Product requirement with full function reliability approved.

DFN3x3 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V^1$	20	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V^1$	5	A
$I_D@T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V^1$	8	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V^1$	4	A
I_{DM}	Pulsed Drain Current ²	25	A
$P_D@T_C=25^\circ C$	Total Power Dissipation ¹	15	W
$P_D@T_A=25^\circ C$	Total Power Dissipation ¹	2	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	12	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	2	$^\circ C/W$



N-Channel Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	20			V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =4.5V, I _D =3A	7	8	10.5	mΩ
		V _{GS} =3.9V, I _D =3A	11	13	15	
		V _{GS} =2.5V, I _D =3A	15	18	22	
		V _{GS} =1.8V, I _D =3A	22	26	30	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	0.4	---	1.0	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =16V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =16V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±12V, V _{DS} =0V	---	---	±10	uA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =3A	---	42	---	S
Q _g	Total Gate Charge (4.5V)	V _{DS} =10V, I _D =3A	---	38	---	nC
	Total Gate Charge (3.9V)		---	33	---	
Q _{gs}	Gate-Source Charge		---	4.5	---	
Q _{gd}	Gate-Drain Charge		---	12	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =16V, V _{GS} =4.5V, R _G =6Ω I _D =3A	---	22	---	ns
T _r	Rise Time		---	41	---	
T _{d(off)}	Turn-Off Delay Time		---	77	---	
T _f	Fall Time		---	21	---	
C _{iss}	Input Capacitance	V _{DS} =10V, V _{GS} =0V, f=1MHz	---	2143	---	pF
C _{oss}	Output Capacitance		---	380	---	
C _{rss}	Reverse Transfer Capacitance		---	325	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _s	Continuous Source Current ¹	V _G =V _D =0V, Force Current	---	---	15	A
I _{SM}	Pulsed Source Current ²		---	---	30	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _s =3A, T _J =25°C	---	---	1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, t ≤10s.
- 2.The data tested by pulsed , pulse width ≤ 10us , duty cycle ≤ 1%

Typical Characteristics

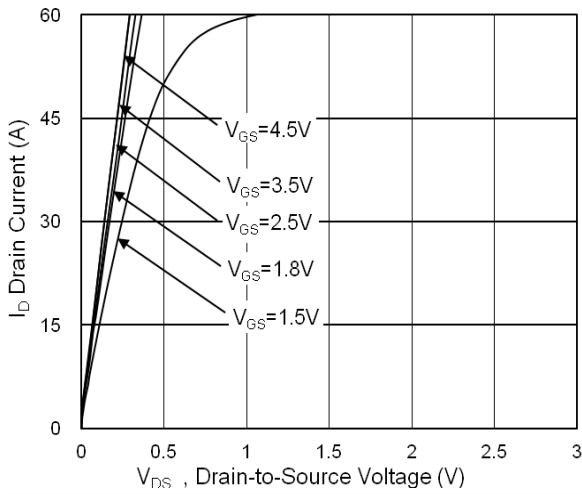


Fig.1 Typical Output Characteristics

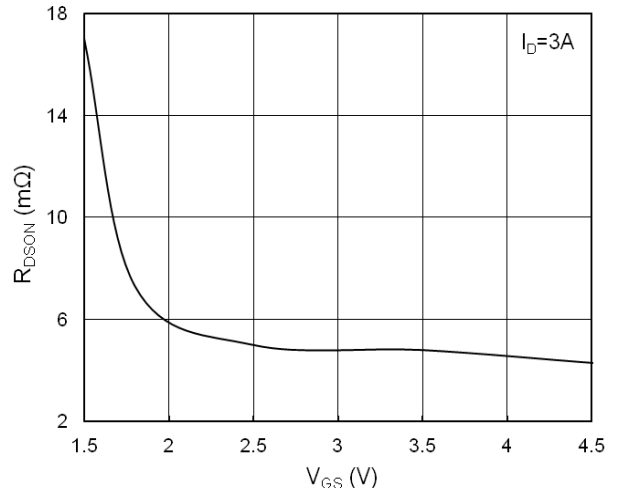


Fig.2 On-Resistance vs. G-S Voltage

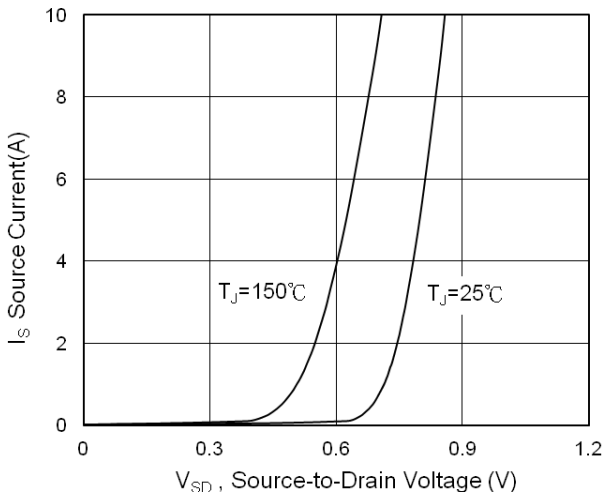


Fig.3 Source-Drain Forward Characteristics

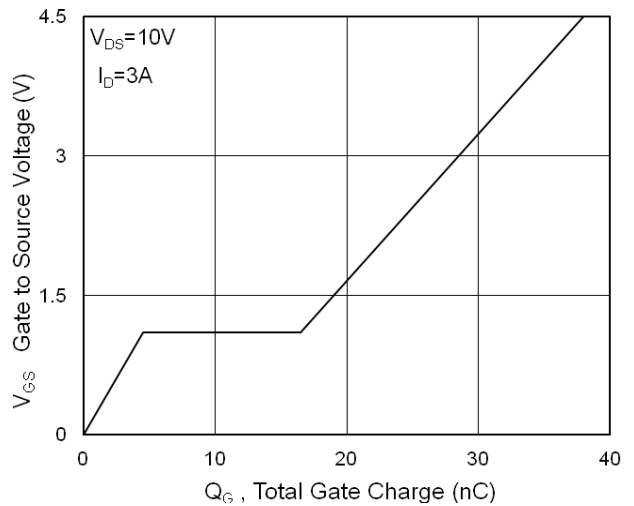


Fig.4 Gate-Charge Characteristics

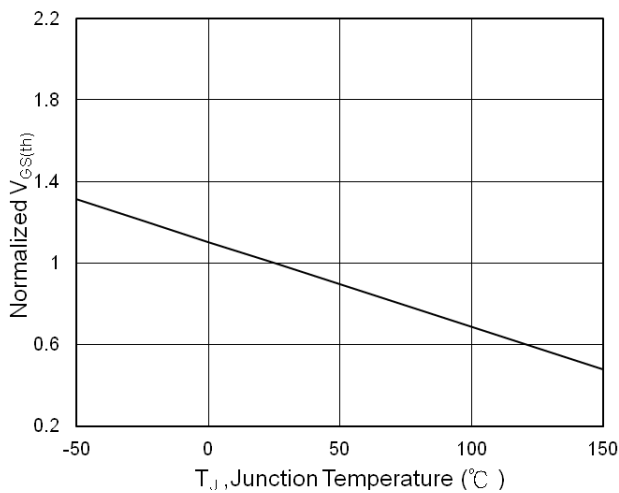


Fig.5 $V_{GS(th)}$ vs. T_J

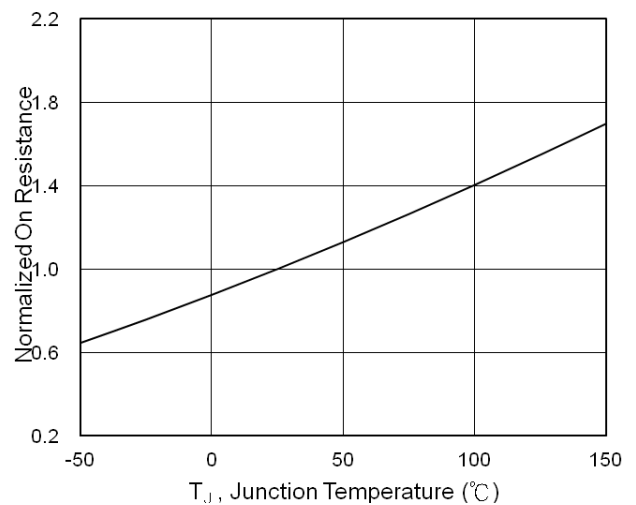
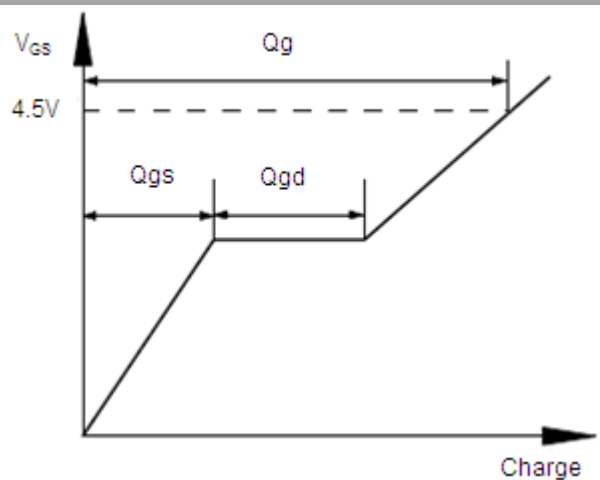
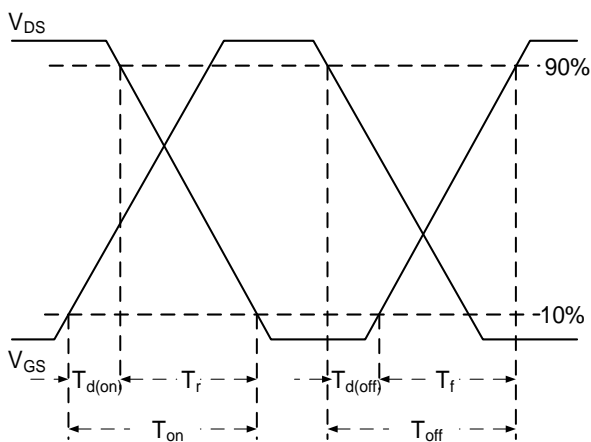
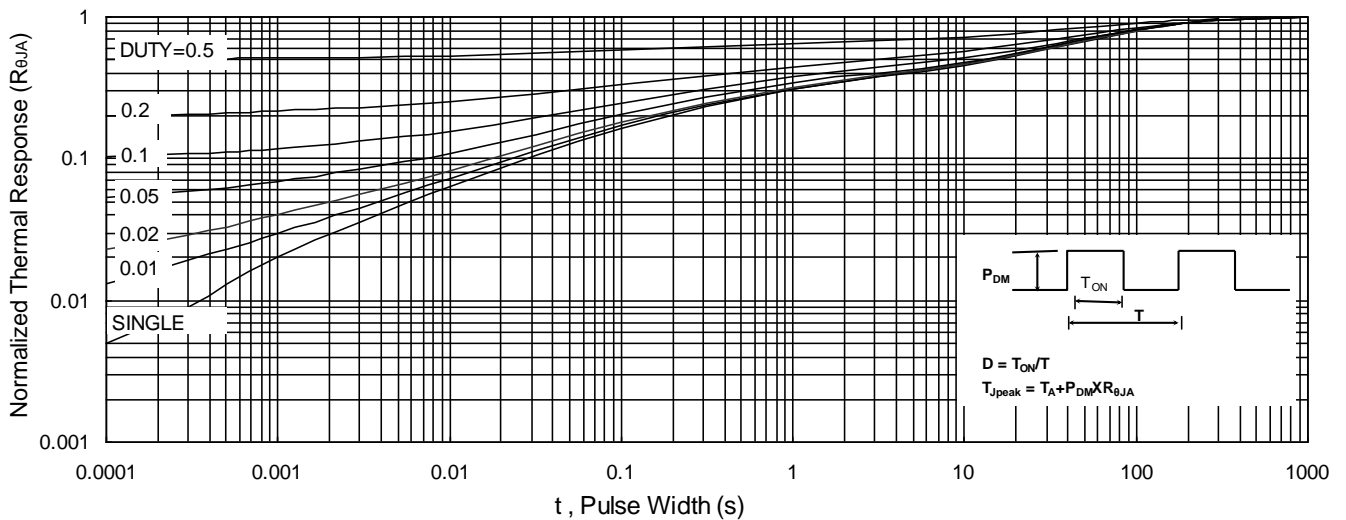
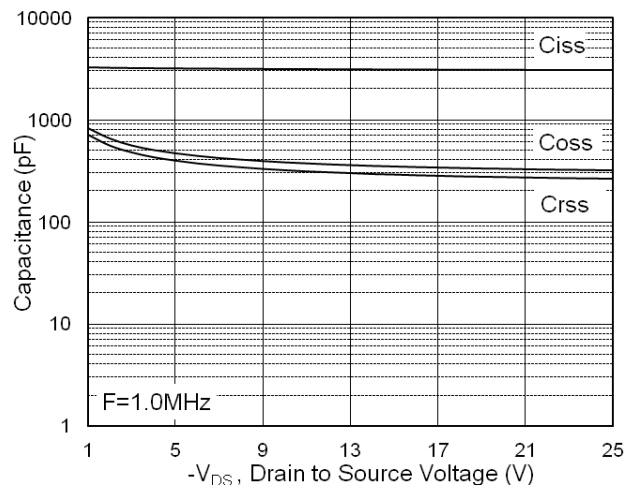
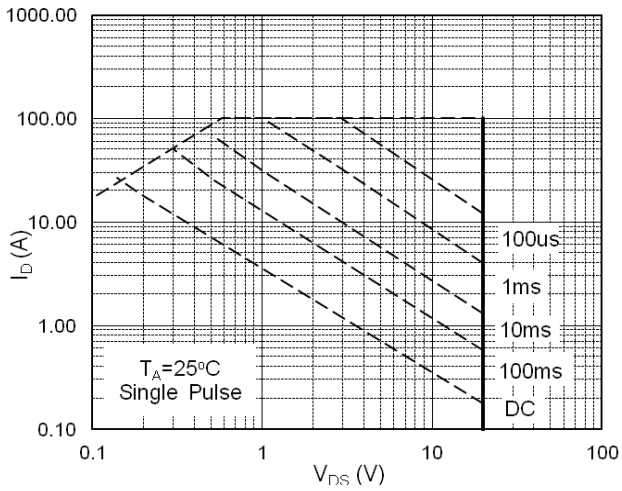
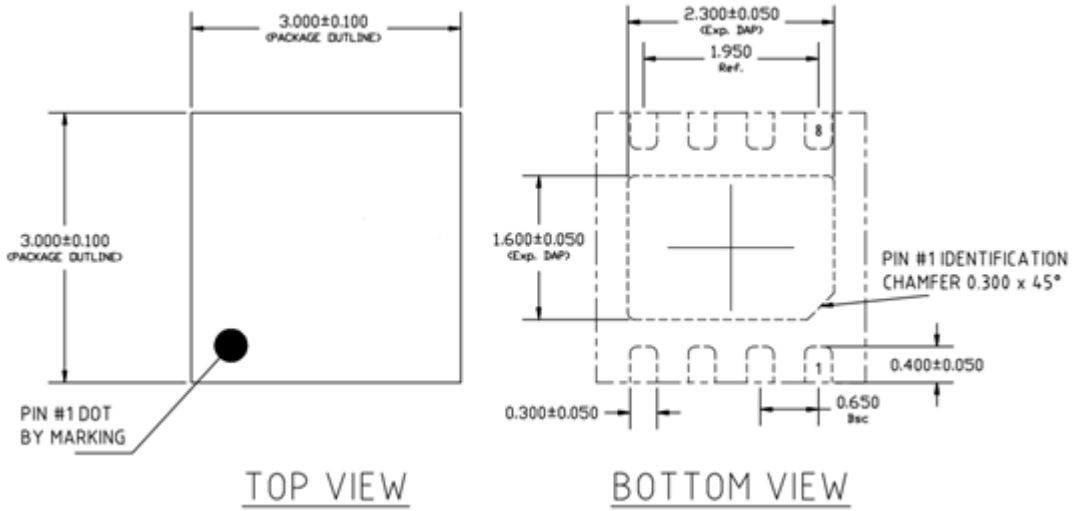


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

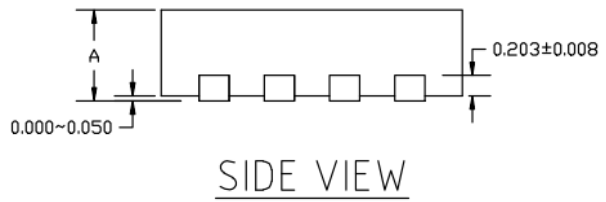
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DFN3x3 Package Outline Dimensions

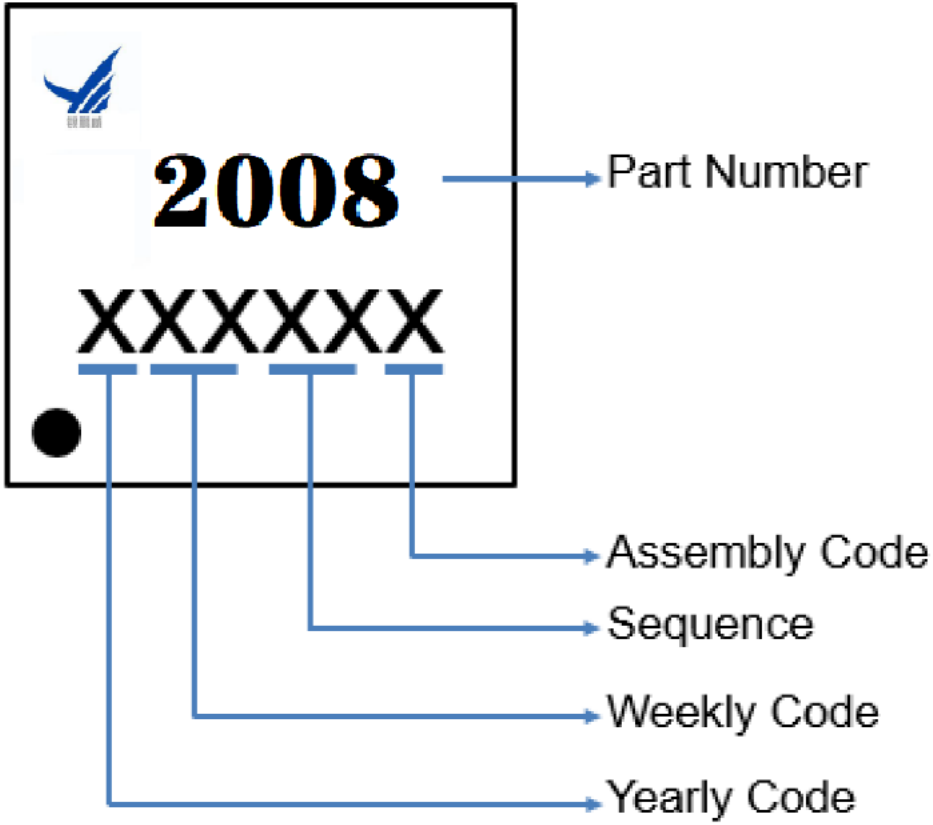


A	MAX.	0.800
	NOM.	0.750
	MIN.	0.700





Marking Instruction



DFN3x3 Tape and Reel Data

